



## **NTE3880 Integrated Circuit NMOS, 8-Bit Microprocessor (MPU), 4MHz**

### **Description:**

The NTE3880 is a third generation single chip microprocessor with unrivaled computational power. This increased computational power results in higher system through-put and more efficient memory utilization when compared to second generation microprocessors. In addition it is very easy to implement into a system because of it's single voltage requirement plus all output signals are fully decoded and timed to control standard memory or peripheral circuits. The circuit is implemented using an N-channel, ion implanted, silicon gate MOS process.

This device has an internal register configuration which contains 208 bits of Read/Write memory that are accessible to the programmer. The registers include two sets of six general purpose registers that may be used individually as 8-bit registers or as 16-bit register pairs. There are also two sets of accumulator and flag registers. The programmer has access to either set of main or alternate registers through a group of exchange instructions. This alternate set allows foreground/background mode of operation or may be reserved for very fast interrupt response. The NTE3880 also contains a 16-bit stack pointer which permits simple implementation of multiple level interrupts, unlimited subroutine nesting and simplification of many types of data handling.

The two 16-bit index registers allow tabular data manipulation and easy implementation of relocatable code. The Refresh register provides for automatic, totally transparent refresh of external dynamic memories. The I register is used in a powerful interrupt response mode to form the upper 8 bits of a pointer to a interrupt service address table, while the interrupting device supplies the lower 8 bits of the pointer. An indirect call is then made to this service address.

### **Features:**

- Single Chip, N-Channel Silicon Gate
- 158 Instructions – Includes all 78 of the 8080A Instructions with Total Software Compatibility. New Instructions Include 4-, 8- and 16-Bit Operations with more useful Addressing Modes such as Indexed, Bit and Relative
- 17 Internal Registers
- Three Modes of Fast Interrupt Response plus a Non-Maskable Interrupt
- Directly Interfaces Standard Speed Static or Dynamic Memories with Virtually No External Logic
- 1.0 $\mu$ s Instruction Execution Speed
- Single 5VDC Supply and Single-Phase 5V Clock
- Out-Performs any other Single-Phase 5V Clock
- All Pins TTL Compatible
- Built-In Dynamic RAM Refresh Circuitry

### Absolute Maximum Ratings:

Temperature Under Bias .....	0° to +70°C
Storage Temperature Range .....	-65° to +150°C
Voltage On Any Pin With Respect to GND .....	-0.3V to +7V
Power Dissipation .....	1.5W

Note 1. Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only functional operation of the device at these or any other condition above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

### DC Characteristics: (T<sub>A</sub> = 0° to 70°C, V<sub>CC</sub> = 5V ±5% unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Clock Input Low Voltage	V <sub>ILC</sub>		-0.3	-	0.80	V
Clock Input High Voltage	V <sub>IHC</sub>		V <sub>CC</sub> -0.6	-	V <sub>CC</sub> +3	V
Input Low Voltage	V <sub>IL</sub>		-0.3	-	0.8	V
Input High Voltage	V <sub>IH</sub>		2.0	-	V <sub>CC</sub>	V
Output Low Voltage	V <sub>OL</sub>	I <sub>OL</sub> = 1.8mA	-	-	0.4	V
Output High Voltage	V <sub>OH</sub>	I <sub>OH</sub> = -250µA	2.4	-	-	V
Power Supply Current	I <sub>CC</sub>		-	90	200	mA
Input Leakage Current	I <sub>L1</sub>	V <sub>IN</sub> = 0 to V <sub>CC</sub>	-	-	10	µA
Tri-State Output Leakage Current in Float	I <sub>LOH</sub>	V <sub>OUT</sub> = 2.4 to V <sub>CC</sub>	-	-	10	µA
Tri-State Output Leakage Current in Float	I <sub>LOL</sub>	V <sub>OUT</sub> = 0.4V	-	-	-10	µA
Data Bus Leakage Current in Input Mode	I <sub>LD</sub>	0 ≤ V <sub>IN</sub> ≤ V <sub>CC</sub>	-	-	±10	µA

### Capacitance: (T<sub>A</sub> = +25°C, f = 1MHz, unmeasured pins to GND unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Clock Capacitance	C <sub>φ</sub>		-	-	35	pF
Input Capacitance	C <sub>IN</sub>		-	-	5	pF
Output Capacitance	C <sub>OUT</sub>		-	-	10	pF

### AC Characteristics: (T<sub>A</sub> = 0°C to +70°C, V<sub>CC</sub> = +15V ± 5% unless otherwise specified)

Parameter	Symbol	Signal	Test Conditions	Min	Typ	Max	Unit
Clock Period	t <sub>c</sub>	φ		25	-	Note 2	µs
Clock Pulse Width, Clock High	t <sub>w</sub> (φH)			110	-	Note 3	ns
Clock Pulse Width, Clock Low	t <sub>w</sub> (φL)			110	-	2000	ns
Clock Rise and Fall Time	t <sub>r</sub> , t <sub>f</sub>			-	-	30	ns
Address Output Delay	t <sub>D</sub> (AD)	A <sub>0-15</sub>	C <sub>L</sub> = 50pF	-	-	110	ns
Data to Float	t <sub>F</sub> (AD)			-	-	90	ns
Address Stable Prior to MRFQ (Memory Cycle)	t <sub>acm</sub>			Note 4	-	-	ns
Address Stable Prior to IOFQ, RD or WR (I/O Cycle)	t <sub>aci</sub>			Note 5	-	-	ns
Address Stable from RD, WR, IORQ, or MREQ	t <sub>ca</sub>			Note 6	-	-	ns
Address Stable from RD or WR During Float	t <sub>caf</sub>			Note 7	-	-	ns

Note 2. t<sub>c</sub> = t<sub>w</sub> (φH) + t<sub>w</sub> (φL) + t<sub>r</sub> + t<sub>f</sub>.

Note 3. Although static by design, testing guarantees t<sub>w</sub> (φH) of 200µs maximum.

Note 4. t<sub>acm</sub> = t<sub>w</sub> (φH) + t<sub>f</sub>-65.

Note 5. t<sub>aci</sub> = t<sub>c</sub>-70.

Note 6. t<sub>ca</sub> = t<sub>w</sub> (φL) + t<sub>r</sub>-50.

Note 7. t<sub>caf</sub> = t<sub>w</sub> (φL) + t<sub>r</sub>-45.

**AC Characteristics (Cont'd):** ( $T_A = 0^\circ\text{C}$  to  $+70^\circ\text{C}$ ,  $V_{CC} = +15\text{V} \pm 5\%$  unless otherwise specified)

Parameter	Symbol	Signal	Test Conditions	Min	Typ	Max	Unit
Data Output Delay	$t_D$ (D)	D <sub>0-7</sub>	$C_L = 50\text{pF}$	—	—	150	ns
Delay to Float During Write Cycle	$t_F$ (D)			—	—	90	ns
Data Setup Time to Rising Edge of Clock During M <sub>1</sub> Cycle	$t_{S\phi}$ (D)			35	—	—	ns
Data Setup Time to falling Edge of Clock During M <sub>2</sub> to M <sub>5</sub>				50	—	—	ns
Data Stable Prior to WR (Memory Cycle)	$t_{dcm}$			Note 8	—	—	ns
Data Stable Prior to WR (I/O Cycle)	$t_{dci}$			Note 9	—	—	ns
Data Stable From WR	$t_{cdf}$			Note 10	—	—	ns
Any Hold Time for Setup Time	$t_H$			—	—	0	ns
MREQ Delay From Falling Edge of Clock, MREQ Low	$t_{DL\phi}$ (MR)	MREQ	$C_L = 50\text{pF}$	—	—	85	ns
MREQ Delay From Rising Edge of Clock, MREQ High	$t_{DH\phi}$ (MR)			—	—	85	ns
MREQ Delay From Falling Edge of Clock, MREQ High				—	—	85	ns
Pulse Width, MREQ Low	$t_w$ (MRL)			Note 11	—	—	ns
Pulse Width, MREQ High	$t_w$ (MRH)			Note 12	—	—	ns
IORQ Delay From Rising Edge of Clock IORQ Low	$t_{DL\phi}$ (IR)	IORQ	$C_L = 50\text{pF}$	—	—	75	ns
IORQ Delay From Falling Edge of Clock IORQ Low				—	—	85	ns
IORQ Delay From Rising Edge of Clock IORQ High	$t_{DH\phi}$ (IR)			—	—	85	ns
IORQ Delay From Falling Edge of Clock IORQ High				—	—	85	ns
RD Delay From Rising Edge of Clock, RD Low	$t_{DL\phi}$ (RD)	RD	$C_L = 50\text{pF}$	—	—	85	ns
RD Delay From Falling Edge of Clock, RD Low				—	—	95	ns
RD Delay From Rising Edge of Clock, RD High	$t_{DH\phi}$ (RD)			—	—	85	ns
RD Delay From Falling Edge of Clock, RD High				—	—	85	ns
WR Delay From Rising Edge of Clock, WR Low	$t_{DL\phi}$ (WR)	WR	$C_L = 50\text{pF}$	—	—	65	ns
WR Delay From Falling Edge of Clock, WR Low				—	—	80	ns
WR Delay From Falling Edge of Clock, WR High	$t_{DH\phi}$ (WR)			—	—	80	ns
Pulse Width, WR Low	$t_w$ (WRL)			Note 13	—	—	ns

Note 8.  $t_{dcm} = t_c - 170$ .

Note 9.  $t_{dci} = t_w(\phi L) + t_r - 170$ .

Note 10.  $t_{cdf} = t_w(\phi L) + t_r - 70$ .

Note 11.  $t_w(\text{MRL}) = t_c - 30$ .

Note 12.  $t_w(\text{MRH}) = t_w(\phi H) + t_r - 20$ .

Note 13.  $t_w(\text{WRL}) = t_c - 30$ .

**AC Characteristics (Cont'd):** ( $T_A = 0^\circ\text{C}$  to  $+70^\circ\text{C}$ ,  $V_{CC} = +15\text{V} \pm 5\%$  unless otherwise specified)

Parameter	Symbol	Signal	Test Conditions	Min	Typ	Max	Unit
M1 Delay From Rising Edge of Clock, M1 Low	$t_{DL}(\text{M1})$	M1	$C_L = 50\text{pF}$	—	—	100	ns
M1 Delay From Rising Edge of Clock, M1 High	$t_{DH}(\text{M1})$			—	—	100	ns
RFSH Delay From Rising Edge of Clock, RFSH Low	$t_{DL}(\text{RF})$	RFSH	$C_L = 50\text{pF}$	—	—	130	ns
RFSH Delay From Rising Edge of Clock, RFSH High	$t_{DH}(\text{RF})$			—	—	120	ns
WAIT Setup Time to Falling Edge of Clock	$t_s(\text{WT})$	WAIT		70	—	—	ns
HALT Delay Time From Falling Edge of Clock	$t_D(\text{HT})$	HALT	$C_L = 50\text{pF}$	—	—	300	ns
INT Setup Time to Rising Edge of Clock	$t_s(\text{IT})$	INT		80	—	—	ns
Pulse Width, NM1 Low	$t_w(\text{NML})$	NM1		80	—	—	ns
BUSRQ Setup Time to Rising Edge of Clock	$t_s(\text{BQ})$	BUSRQ		50	—	—	ns
BUSAk Delay From Rising Edge of Clock, BUSAK Low	$t_{DL}(\text{BA})$	BUSAk	$C_L = 50\text{pF}$	—	—	100	ns
BUSAk Delay From Rising Edge of Clock, BUSAK High	$t_{DH}(\text{BA})$			—	—	100	ns
RESET Setup Time to Rising Edge of Clock	$t_s(\text{RS})$	RESET		60	—	—	ns
Delay to Float (MREQ, IORQ, RD and WR)	$t_F(\text{C})$			—	—	80	ns
M1 Stable Prior to IORQ (Interrupt Ack.)	$t_{mr}$			Note 14	—	—	ns

Note 14.  $t_{mr} = 2t_c + t_w(\phi\text{H}) + t_f - 65$ .

Note 15. Data should be enabled onto the CPU data bus when  $\overline{RD}$  is active. During interrupt acknowledge data should be enabled when M1 and  $\overline{IORQ}$  are both active.

Note 16. All control signals are internally synchronized, so they may be totally asynchronous with respect to the clock.

Note 17. The RESET signal must be active for a minimum of 3 clock cycles.

Note 18. Output Delay vs. Loaded Capacitance

$T_A = +70^\circ\text{C}$     $V_{CC} = 5\text{V} \pm 5\%$

Add 10ns delay for each 50pF increase in load up to maximum of 200pF for data bus and 100pF for address & control lines.



